



PATENT NUMBER

U.S. UTILITY Patent Application
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APPLICATION NO. 09/955600		CONT/PRIOR D F	CLASS 438	SUBCLASS	ART UNIT 2813	Tuan Namen
APPLICANIS	Nobuhiko H Takashi Ka		,	·-	.:	
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	ISSUING CLA	SSIFICATION
ORIGINAL	· 100 100 100 100 100 100 100 100 100 10	CROSS REFERENCE(S)
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TERMINAL	DRAWINGS		CLIAIMS ALLOWED
DISCLAIMER	Sheets Drwg. Figs. Drwg.	Print Fig.	Total Claims Rrint Claim for O.G.
The term of this patent subsequent to(date)			NOTICE OF ALLOWANCE MAILED
has been disclaimed.	(Assistant Examiner)	(Date)	
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